74AUP1G04-Q100

Low-power inverter

Rev. 1 — 18 November 2013 | Product data sheet

1. General description

The 74AUP1G04-Q100 provides the single inverting buffer.

Schmitt-trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial Power-down applications using I_{OFF}. The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
  - Specified from –40 °C to +85 °C and from –40 °C to +125 °C
- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
  - JESD8-12 (0.8 V to 1.3 V)
  - JESD8-11 (0.9 V to 1.65 V)
  - JESD8-7 (1.2 V to 1.95 V)
  - JESD8-5 (1.8 V to 2.7 V)
  - JESD8-B (2.7 V to 3.6 V)
- ESD protection:
  - MIL-STD-883, method 3015 Class 3A. Exceeds 5000 V
  - HBM JESD22-A114F Class 3A. Exceeds 5000 V
  - MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- Low static power consumption; I_{CC} = 0.9 μA (maximum)
- Latch-up performance exceeds 100 mA per JESD 78B Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AUP1G04GW-Q100	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1
74AUP1G04GV-Q100	–40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753

4. Marking

Table 2. Marking

Type number	Marking code[1]
74AUP1G04GV-Q100	p04
74AUP1G04GW-Q100	pC

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram

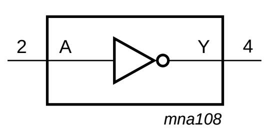

Fig 1. Logic symbol

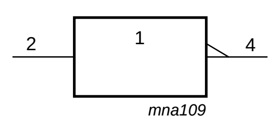

Fig 2. IEC logic symbol

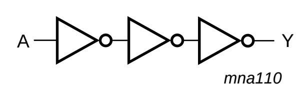

Fig 3. Logic diagram

6. Pinning information

6.1 Pinning

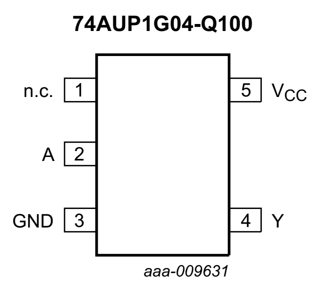

Fig 4. Pin configuration SOT353-1 and SOT753

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6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
n.c.	1	not connected
A	2	data input
GND	3	ground (0 V)
Y	4	data output
V_{CC}	5	supply voltage

7. Functional description

Table 4. Function table[1]

Input	Output
A	**Y**
L	H
H	L

[1] H = HIGH voltage level; L = LOW voltage level.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			–0.5	+4.6	V
I_{IK}	input clamping current	$V_I < 0$ V		–50	-	mA
V_I	input voltage		[1]	–0.5	+4.6	V
I_{OK}	output clamping current	$V_O < 0$ V		–50	-	mA
V_O	output voltage	active mode	[1]	–0.5	V_{CC} + 0.5	V
		power-down mode	[1]	–0.5	+4.6	V
I_O	output current	V_O = 0 V to V_{CC}		-	±20	mA
I_{CC}	supply current			-	+50	mA
I_{GND}	ground current			–50	-	mA
T_{stg}	storage temperature			–65	+150	°C
P_{tot}	total power dissipation	T_{amb} = –40 °C to +125 °C	[2]	-	250	mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP5 and SC-74A packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K.

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9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		0.8	3.6	V
V_I	input voltage		0	3.6	V
V_O	output voltage	active mode	0	V_{CC}	V
		power-down mode; V_{CC} = 0 V	0	3.6	V
T_{amb}	ambient temperature		–40	+125	°C
Δt/ΔV	input transition rise and fall rate	V_{CC} = 0.8 V to 3.6 V	0	200	ns/V

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = 25 °C						
V_{IH}	HIGH-level input voltage	V_{CC} = 0.8 V	0.70 × V_{CC}	-	-	V
		V_{CC} = 0.9 V to 1.95 V	0.65 × V_{CC}	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V_{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 0.8 V	-	-	0.30 × V_{CC}	V
		V_{CC} = 0.9 V to 1.95 V	-	-	0.35 × V_{CC}	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V_{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V_{OH}	HIGH-level output voltage	V_I = V_{IH} or V_{IL}				
		I_O = –20 μA; V_{CC} = 0.8 V to 3.6 V	V_{CC} – 0.1	-	-	V
		I_O = –1.1 mA; V_{CC} = 1.1 V	0.75 × V_{CC}	-	-	V
		I_O = –1.7 mA; V_{CC} = 1.4 V	1.11	-	-	V
		I_O = –1.9 mA; V_{CC} = 1.65 V	1.32	-	-	V
		I_O = –2.3 mA; V_{CC} = 2.3 V	2.05	-	-	V
		I_O = –3.1 mA; V_{CC} = 2.3 V	1.9	-	-	V
		I_O = –2.7 mA; V_{CC} = 3.0 V	2.72	-	-	V
		I_O = –4.0 mA; V_{CC} = 3.0 V	2.6	-	-	V
V_{OL}	LOW-level output voltage	V_I = V_{IH} or V_{IL}				
		I_O = 20 μA; V_{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I_O = 1.1 mA; V_{CC} = 1.1 V	-	-	0.3 × V_{CC}	V
		I_O = 1.7 mA; V_{CC} = 1.4 V	-	-	0.31	V
		I_O = 1.9 mA; V_{CC} = 1.65 V	-	-	0.31	V
		I_O = 2.3 mA; V_{CC} = 2.3 V	-	-	0.31	V
		I_O = 3.1 mA; V_{CC} = 2.3 V	-	-	0.44	V
		I_O = 2.7 mA; V_{CC} = 3.0 V	-	-	0.31	V
		I_O = 4.0 mA; V_{CC} = 3.0 V	-	-	0.44	V

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Table 7. Static characteristics *…continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_I	input leakage current	V_I = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.1	μA
I_{OFF}	power-off leakage current	V_I or V_O = 0 V to 3.6 V; V_{CC} = 0 V	-	-	±0.2	μA
ΔI_{OFF}	additional power-off leakage current	V_I or V_O = 0 V to 3.6 V; V_{CC} = 0 V to 0.2 V	-	-	±0.2	μA
I_{CC}	supply current	V_I = GND or V_{CC}; I_O = 0 A; V_{CC} = 0.8 V to 3.6 V	-	-	0.5	μA
ΔI_{CC}	additional supply current	$V_I = V_{CC} - 0.6$ V; I_O = 0 A; V_{CC} = 3.3 V	-	-	40	μA
C_I	input capacitance	V_{CC} = 0 V to 3.6 V; V_I = GND or V_{CC}	-	0.8	-	pF
C_O	output capacitance	V_O = GND; V_{CC} = 0 V	-	1.7	-	pF
T_{amb} = −40 °C to +85 °C						
V_{IH}	HIGH-level input voltage	V_{CC} = 0.8 V	$0.70 \times V_{CC}$	-	-	V
		V_{CC} = 0.9 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V_{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 0.8 V	-	-	$0.30 \times V_{CC}$	V
		V_{CC} = 0.9 V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V_{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		I_O = −20 μA; V_{CC} = 0.8 V to 3.6 V	$V_{CC} - 0.1$	-	-	V
		I_O = −1.1 mA; V_{CC} = 1.1 V	$0.7 \times V_{CC}$	-	-	V
		I_O = −1.7 mA; V_{CC} = 1.4 V	1.03	-	-	V
		I_O = −1.9 mA; V_{CC} = 1.65 V	1.30	-	-	V
		I_O = −2.3 mA; V_{CC} = 2.3 V	1.97	-	-	V
		I_O = −3.1 mA; V_{CC} = 2.3 V	1.85	-	-	V
		I_O = −2.7 mA; V_{CC} = 3.0 V	2.67	-	-	V
		I_O = −4.0 mA; V_{CC} = 3.0 V	2.55	-	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		I_O = 20 μA; V_{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I_O = 1.1 mA; V_{CC} = 1.1 V	-	-	$0.3 \times V_{CC}$	V
		I_O = 1.7 mA; V_{CC} = 1.4 V	-	-	0.37	V
		I_O = 1.9 mA; V_{CC} = 1.65 V	-	-	0.35	V
		I_O = 2.3 mA; V_{CC} = 2.3 V	-	-	0.33	V
		I_O = 3.1 mA; V_{CC} = 2.3 V	-	-	0.45	V
		I_O = 2.7 mA; V_{CC} = 3.0 V	-	-	0.33	V
		I_O = 4.0 mA; V_{CC} = 3.0 V	-	-	0.45	V
I_I	input leakage current	V_I = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.5	μA
I_{OFF}	power-off leakage current	V_I or V_O = 0 V to 3.6 V; V_{CC} = 0 V	-	-	±0.5	μA
ΔI_{OFF}	additional power-off leakage current	V_I or V_O = 0 V to 3.6 V; V_{CC} = 0 V to 0.2 V	-	-	±0.6	μA

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Table 7. Static characteristics *…continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{CC}	supply current	V_I = GND or V_{CC}; I_O = 0 A; V_{CC} = 0.8 V to 3.6 V	-	-	0.9	μA
ΔI_{CC}	additional supply current	$V_I = V_{CC} - 0.6$ V; I_O = 0 A; V_{CC} = 3.3 V	-	-	50	μA
T_{amb} = −40 °C to +125 °C						
V_{IH}	HIGH-level input voltage	V_{CC} = 0.8 V	0.75 × V_{CC}	-	-	V
		V_{CC} = 0.9 V to 1.95 V	0.70 × V_{CC}	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V_{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 0.8 V	-	-	0.25 × V_{CC}	V
		V_{CC} = 0.9 V to 1.95 V	-	-	0.30 × V_{CC}	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V_{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		I_O = −20 μA; V_{CC} = 0.8 V to 3.6 V	V_{CC} − 0.11	-	-	V
		I_O = −1.1 mA; V_{CC} = 1.1 V	0.6 × V_{CC}	-	-	V
		I_O = −1.7 mA; V_{CC} = 1.4 V	0.93	-	-	V
		I_O = −1.9 mA; V_{CC} = 1.65 V	1.17	-	-	V
		I_O = −2.3 mA; V_{CC} = 2.3 V	1.77	-	-	V
		I_O = −3.1 mA; V_{CC} = 2.3 V	1.67	-	-	V
		I_O = −2.7 mA; V_{CC} = 3.0 V	2.40	-	-	V
		I_O = −4.0 mA; V_{CC} = 3.0 V	2.30	-	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		I_O = 20 μA; V_{CC} = 0.8 V to 3.6 V	-	-	0.11	V
		I_O = 1.1 mA; V_{CC} = 1.1 V	-	-	0.33 × V_{CC}	V
		I_O = 1.7 mA; V_{CC} = 1.4 V	-	-	0.41	V
		I_O = 1.9 mA; V_{CC} = 1.65 V	-	-	0.39	V
		I_O = 2.3 mA; V_{CC} = 2.3 V	-	-	0.36	V
		I_O = 3.1 mA; V_{CC} = 2.3 V	-	-	0.50	V
		I_O = 2.7 mA; V_{CC} = 3.0 V	-	-	0.36	V
		I_O = 4.0 mA; V_{CC} = 3.0 V	-	-	0.50	V
I_I	input leakage current	V_I = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.75	μA
I_{OFF}	power-off leakage current	V_I or V_O = 0 V to 3.6 V; V_{CC} = 0 V	-	-	±0.75	μA
ΔI_{OFF}	additional power-off leakage current	V_I or V_O = 0 V to 3.6 V; V_{CC} = 0 V to 0.2 V	-	-	±0.75	μA
I_{CC}	supply current	V_I = GND or V_{CC}; I_O = 0 A; V_{CC} = 0.8 V to 3.6 V	-	-	1.4	μA
ΔI_{CC}	additional supply current	$V_I = V_{CC} - 0.6$ V; I_O = 0 A; V_{CC} = 3.3 V	-	-	75	μA

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11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit, see Figure 6

Symbol	Parameter	Conditions		Min	Typ [1]	Max	Unit
T_{amb} = 25 °C; C_L = 5 pF							
t_{pd}	propagation delay	A to Y; see Figure 5	[2]				
		V_{CC} = 0.8 V		-	16.0	-	ns
		V_{CC} = 1.1 V to 1.3 V		2.4	5.0	10.3	ns
		V_{CC} = 1.4 V to 1.6 V		1.8	3.6	6.4	ns
		V_{CC} = 1.65 V to 1.95 V		1.5	2.9	5.0	ns
		V_{CC} = 2.3 V to 2.7 V		1.2	2.4	3.9	ns
		V_{CC} = 3.0 V to 3.6 V		1.1	2.1	3.2	ns
T_{amb} = 25 °C; C_L = 10 pF							
t_{pd}	propagation delay	A to Y; see Figure 5	[2]				
		V_{CC} = 0.8 V		-	19.8	-	ns
		V_{CC} = 1.1 V to 1.3 V		2.8	5.9	12.2	ns
		V_{CC} = 1.4 V to 1.6 V		2.3	4.2	7.5	ns
		V_{CC} = 1.65 V to 1.95 V		2.0	3.5	5.9	ns
		V_{CC} = 2.3 V to 2.7 V		1.7	2.9	4.6	ns
		V_{CC} = 3.0 V to 3.6 V		1.6	2.7	3.8	ns
T_{amb} = 25 °C; C_L = 15 pF							
t_{pd}	propagation delay	A to Y; see Figure 5	[2]				
		V_{CC} = 0.8 V		-	23.3	-	ns
		V_{CC} = 1.1 V to 1.3 V		3.2	6.7	13.0	ns
		V_{CC} = 1.4 V to 1.6 V		2.6	4.7	8.6	ns
		V_{CC} = 1.65 V to 1.95 V		2.3	4.0	6.7	ns
		V_{CC} = 2.3 V to 2.7 V		2.1	3.3	5.1	ns
		V_{CC} = 3.0 V to 3.6 V		2.0	3.1	4.2	ns
T_{amb} = 25 °C; C_L = 30 pF							
t_{pd}	propagation delay	A to Y; see Figure 5	[2]				
		V_{CC} = 0.8 V		-	33.6	-	ns
		V_{CC} = 1.1 V to 1.3 V		4.4	8.9	16.0	ns
		V_{CC} = 1.4 V to 1.6 V		3.6	6.3	10.8	ns
		V_{CC} = 1.65 V to 1.95 V		3.2	5.3	9.0	ns
		V_{CC} = 2.3 V to 2.7 V		2.9	4.5	6.5	ns
		V_{CC} = 3.0 V to 3.6 V		2.9	4.2	5.4	ns

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Table 8. Dynamic characteristics *...continued*

Voltages are referenced to GND (ground = 0 V); for test circuit, see Figure 6

Symbol	Parameter	Conditions		Min	Typ [1]	Max	Unit
T_{amb} = 25 °C							
C_{PD}	power dissipation capacitance	f = 1 MHz; V_I = GND to V_{CC}	[3]				
		V_{CC} = 0.8 V		-	2.5	-	pF
		V_{CC} = 1.1 V to 1.3 V		-	2.7	-	pF
		V_{CC} = 1.4 V to 1.6 V		-	2.8	-	pF
		V_{CC} = 1.65 V to 1.95 V		-	3.0	-	pF
		V_{CC} = 2.3 V to 2.7 V		-	3.5	-	pF
		V_{CC} = 3.0 V to 3.6 V		-	4.0	-	pF

[1] All typical values are measured at nominal V_{CC}.

[2] t_{pd} is the same as t_{PLH} and t_{PHL}.

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

Table 9. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit, see Figure 6

Symbol	Parameter	Conditions		–40 °C to +85 °C		–40 °C to +125 °C		Unit
				Min	Max	Min	Max	
C_L = 5 pF								
t_{pd}	propagation delay	A to Y; see Figure 5	[1]					
		V_{CC} = 1.1 V to 1.3 V		2.1	11.4	2.1	12.6	ns
		V_{CC} = 1.4 V to 1.6 V		1.6	7.4	1.6	8.2	ns
		V_{CC} = 1.65 V to 1.95 V		1.4	5.9	1.4	6.5	ns
		V_{CC} = 2.3 V to 2.7 V		1.1	4.5	1.1	5.0	ns
		V_{CC} = 3.0 V to 3.6 V		1.0	3.9	1.0	4.3	ns
C_L = 10 pF								
t_{pd}	propagation delay	A to Y; see Figure 5	[1]					
		V_{CC} = 1.1 V to 1.3 V		2.6	13.7	2.6	15.1	ns
		V_{CC} = 1.4 V to 1.6 V		2.1	8.7	2.1	9.6	ns
		V_{CC} = 1.65 V to 1.95 V		1.8	7.0	1.8	7.7	ns
		V_{CC} = 2.3 V to 2.7 V		1.5	5.4	1.5	6.0	ns
		V_{CC} = 3.0 V to 3.6 V		1.4	4.5	1.4	5.0	ns

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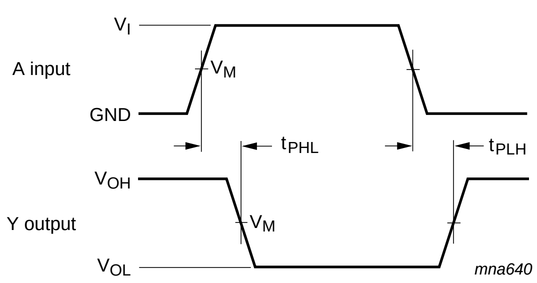
Table 9. Dynamic characteristics *...continued*

Voltages are referenced to GND (ground = 0 V); for test circuit, see Figure 6

Symbol	Parameter	Conditions		–40 °C to +85 °C		–40 °C to +125 °C		Unit
				Min	Max	Min	Max	
C_L = 15 pF								
t_{pd}	propagation delay	A to Y; see Figure 5	[1]					
		V_{CC} = 1.1 V to 1.3 V		3.0	15.8	3.0	17.4	ns
		V_{CC} = 1.4 V to 1.6 V		2.4	10.0	2.4	11.0	ns
		V_{CC} = 1.65 V to 1.95 V		2.1	8.0	2.1	8.8	ns
		V_{CC} = 2.3 V to 2.7 V		1.8	6.1	1.8	6.8	ns
		V_{CC} = 3.0 V to 3.6 V		1.8	5.0	1.8	5.5	ns
C_L = 30 pF								
t_{pd}	propagation delay	A to Y; see Figure 5	[1]					
		V_{CC} = 1.1 V to 1.3 V		4.0	19.0	4.0	20.9	ns
		V_{CC} = 1.4 V to 1.6 V		3.2	12.9	3.2	14.2	ns
		V_{CC} = 1.65 V to 1.95 V		2.9	10.5	2.9	11.6	ns
		V_{CC} = 2.3 V to 2.7 V		2.6	7.6	2.6	8.4	ns
		V_{CC} = 3.0 V to 3.6 V		2.6	6.2	2.6	6.9	ns

[1] t_{pd} is the same as t_{PLH} and t_{PHL}.

12. Waveforms



Measurement points are given in Table 10.

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 5. The data input (A) to output (Y) propagation delays

Table 10. Measurement points

Supply voltage	Output	Input		
V_{CC}	V_M	V_M	V_I	$t_r = t_f$
0.8 V to 3.6 V	0.5 × V_{CC}	0.5 × V_{CC}	V_{CC}	≤ 3.0 ns

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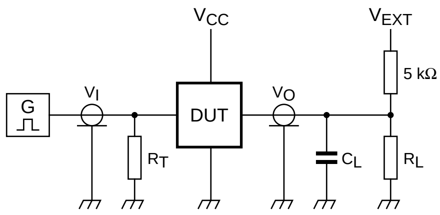

Test data is given in Table 11.

Definitions for test circuit:

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance

R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator

V_{EXT} = External voltage for measuring switching times.

Fig 6. Load circuitry for switching times

Table 11. Test data

Supply voltage	Load		V_{EXT}		
V_{CC}	C_L	R_L [1]	t_{PLH}, t_{PHL}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 kΩ or 1 MΩ	open	GND	2 × V_{CC}

[1] For measuring enable and disable times, R_L = 5 kΩ. For measuring propagation delays, setup and hold times, and pulse width R_L = 1 MΩ.

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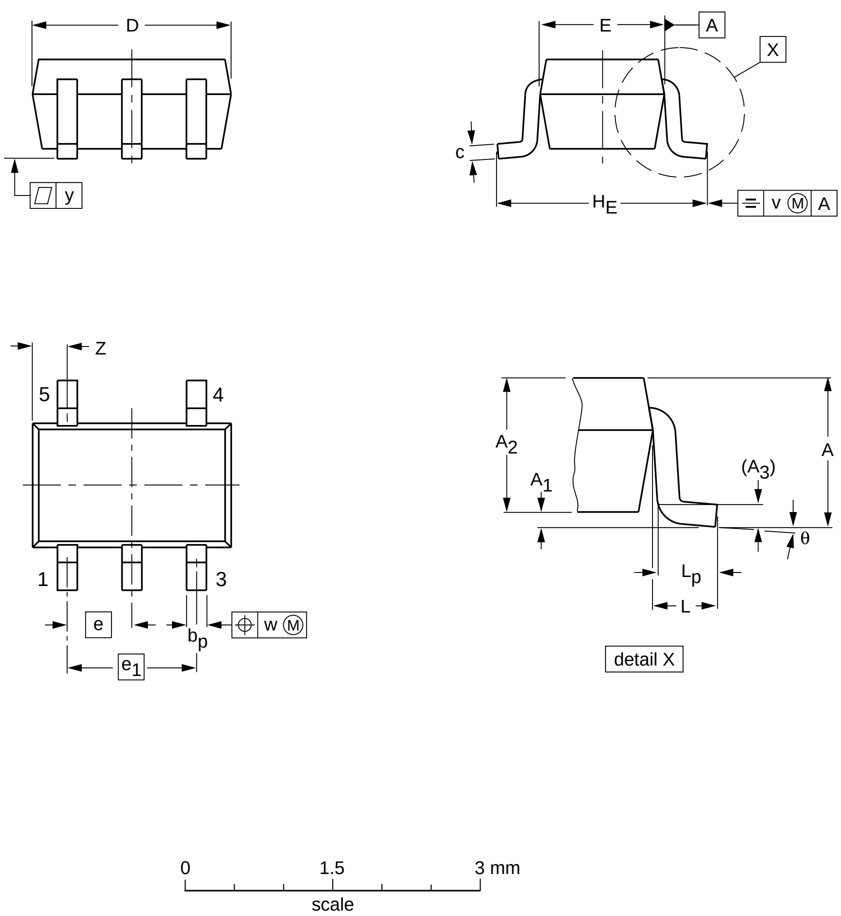
13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm **SOT353-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D(1)	E(1)	e	e_1	H_E	L	L_p	v	w	y	Z(1)	θ
mm	1.1	0.1 0	1.0 0.8	0.15	0.30 0.15	0.25 0.08	2.25 1.85	1.35 1.15	0.65	1.3	2.25 2.0	0.425	0.46 0.21	0.3	0.1	0.1	0.60 0.15	7° 0°

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT353-1		MO-203	SC-88A			~~00-09-01~~ 03-02-19

Fig 7. Package outline SOT353-1 (TSSOP5)

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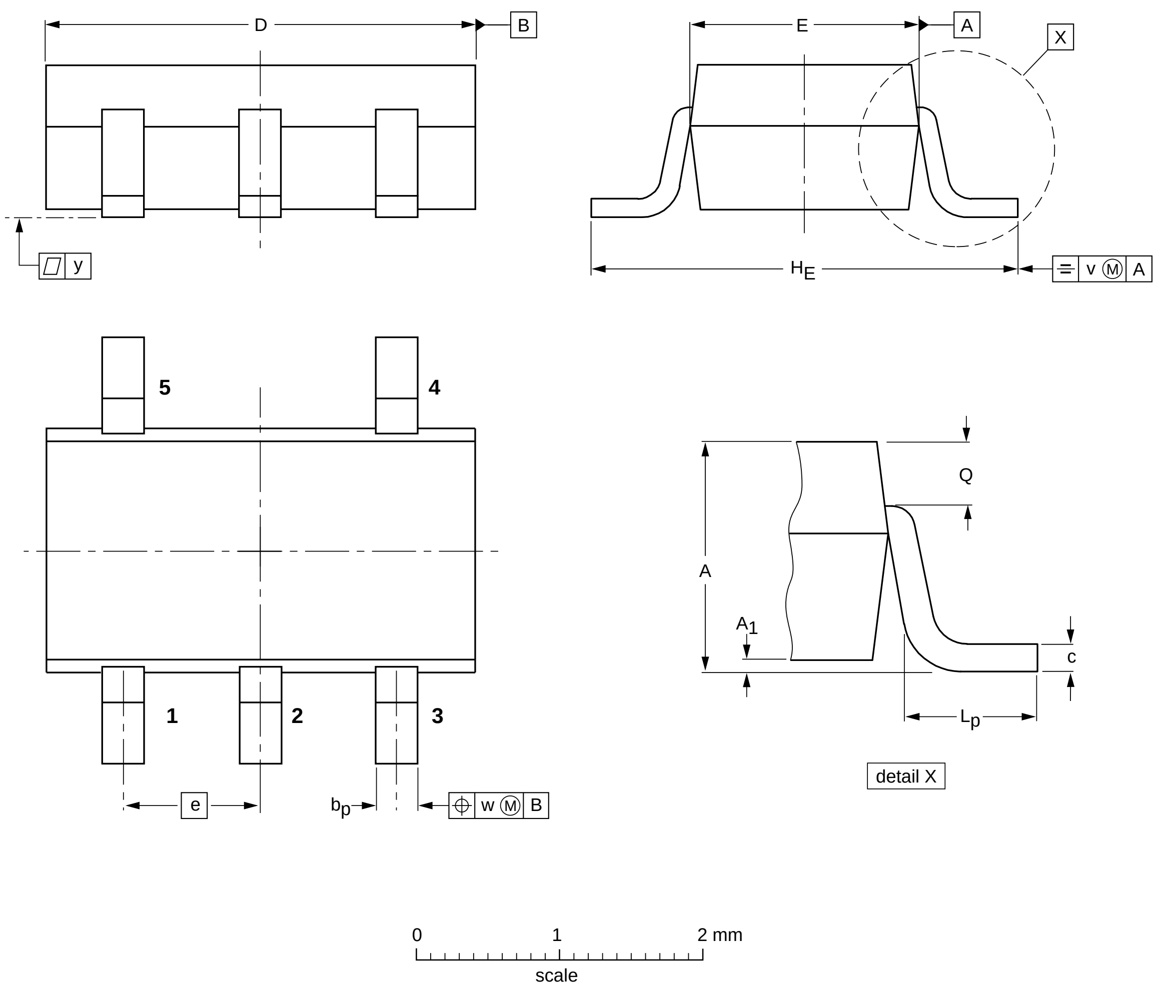
Plastic surface-mounted package; 5 leads **SOT753**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b_p	c	D	E	e	H_E	L_p	Q	v	w	y
mm	1.1 0.9	0.100 0.013	0.40 0.25	0.26 0.10	3.1 2.7	1.7 1.3	0.95	3.0 2.5	0.6 0.2	0.33 0.23	0.2	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT753			SC-74A			~~02-04-16~~ 06-03-16

Fig 8. Package outline SOT753 (SC-74A)

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14. Abbreviations

Table 12. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MIL	Military
MM	Machine Model

15. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP1G04_Q100 v.1	20131118	Product data sheet	-	-

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16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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